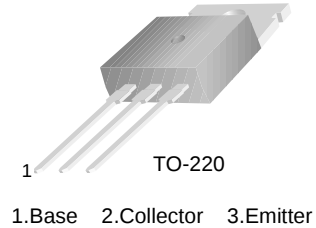


# KSB834

KSB834

## Low Frequency Power Amplifier

- Complement to KSD880



## PNP Silicon Epitaxial Transistor

### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol    | Parameter                                        | Value      | Units            |
|-----------|--------------------------------------------------|------------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                           | - 60       | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                        | - 60       | V                |
| $V_{EBO}$ | Emitter-Base Voltage                             | - 7        | V                |
| $I_C$     | Collector Current                                | - 3        | A                |
| $I_B$     | Base Current                                     | - 0.5      | A                |
| $P_C$     | Collector Dissipation ( $T_C=25^\circ\text{C}$ ) | 30         | W                |
| $P_C$     | Collector Dissipation ( $T_a=25^\circ\text{C}$ ) | 1.5        | W                |
| $T_J$     | Junction Temperature                             | 150        | $^\circ\text{C}$ |
| $T_{STG}$ | Storage Temperature                              | - 55 ~ 150 | $^\circ\text{C}$ |

### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol                 | Parameter                            | Test Condition                                                                                    | Min.     | Typ.  | Max.  | Units         |
|------------------------|--------------------------------------|---------------------------------------------------------------------------------------------------|----------|-------|-------|---------------|
| $I_{CBO}$              | Collector Cut-off Current            | $V_{CB} = -60\text{V}, I_E = 0$                                                                   |          |       | - 100 | $\mu\text{A}$ |
| $I_{EBO}$              | Emitter Cut-off Current              | $V_{EB} = -7\text{V}, I_C = 0$                                                                    |          |       | - 100 | $\mu\text{A}$ |
| $BV_{CEO}$             | Collector-Emitter Breakdown Voltage  | $I_C = -50\text{mA}, I_B = 0$                                                                     | - 60     |       |       | V             |
| $h_{FE1}$<br>$h_{FE2}$ | DC Current Gain                      | $V_{CE} = -5\text{V}, I_C = -0.5\text{A}$<br>$V_{CE} = -5\text{V}, I_C = -3\text{A}$              | 60<br>20 |       | 200   |               |
| $V_{CE(sat)}$          | Collector-Emitter Saturation Voltage | $I_C = -3\text{A}, I_B = -0.3\text{A}$                                                            |          | - 0.5 | - 1   | V             |
| $V_{BE(on)}$           | Base-Emitter ON Voltage              | $V_{CE} = -5\text{V}, I_C = -0.5\text{A}$                                                         |          | - 0.7 | - 1   | V             |
| $f_T$                  | Current Gain Bandwidth Product       | $V_{CE} = -5\text{V}, I_C = -0.5\text{A}$                                                         |          | 9     |       | MHz           |
| $C_{ob}$               | Output Capacitance                   | $V_{CB} = -10\text{V}, I_E = 0$<br>$f = 1\text{MHz}$                                              |          | 150   |       | pF            |
| $t_{ON}$               | Turn ON Time                         | $V_{CC} = -30\text{V}, I_C = -1\text{A}$<br>$I_{B1} = -I_{B2} = -0.2\text{A}$<br>$R_L = 30\Omega$ |          | 0.4   |       | $\mu\text{s}$ |
| $T_{STG}$              | Storage Time                         |                                                                                                   |          | 1.7   |       | $\mu\text{s}$ |
| $t_F$                  | Fall Time                            |                                                                                                   |          | 0.5   |       | $\mu\text{s}$ |

### $h_{FE}$ Classification

| Classification | O        | Y         |
|----------------|----------|-----------|
| $h_{FE1}$      | 60 ~ 120 | 100 ~ 200 |

## Typical Characteristics

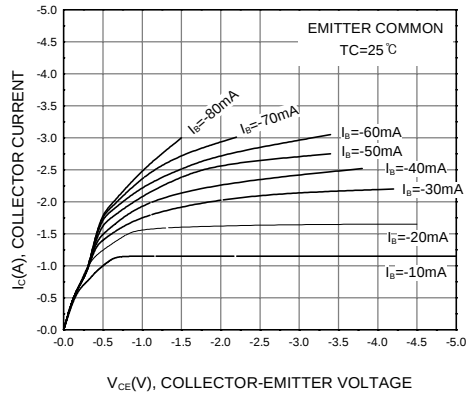


Figure 1. Static Characteristic

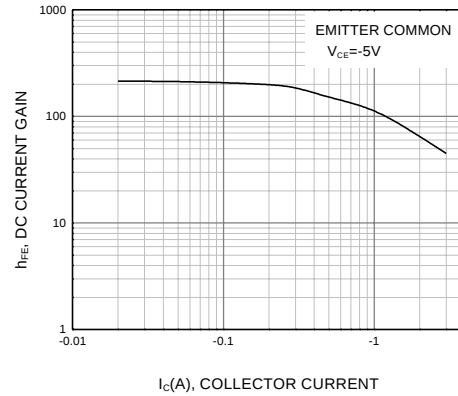


Figure 2. DC current Gain

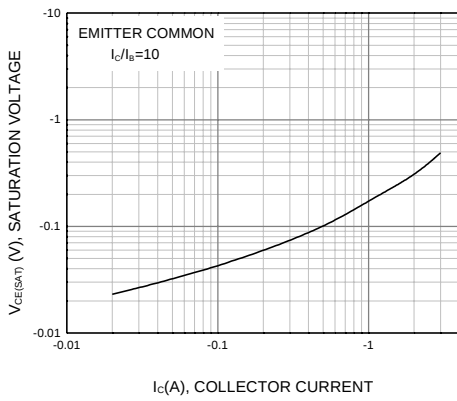


Figure 3. Collector-Emitter Saturation Voltage

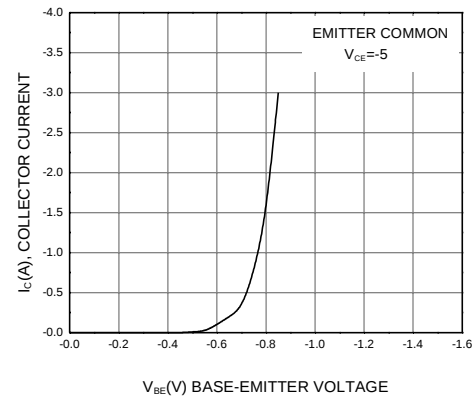


Figure 4. Base-Emitter On Voltage

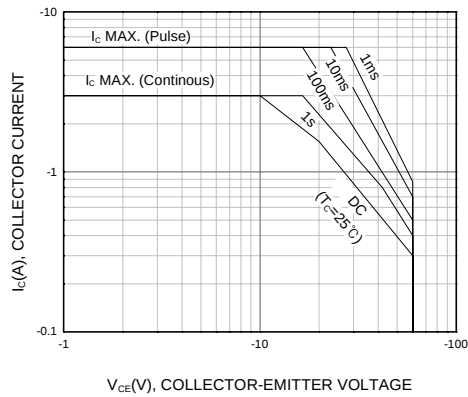


Figure 5. Safe Operating Area

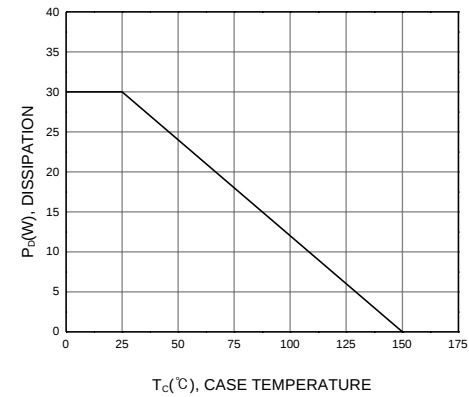
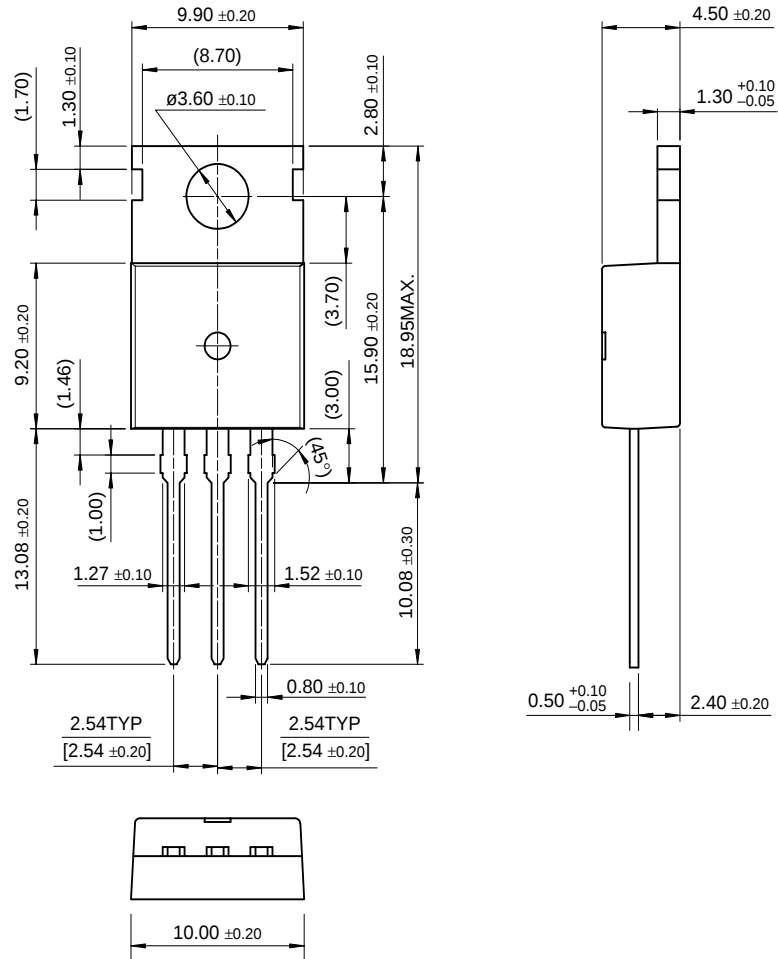


Figure 6. Power Derating

# Package Dimensions

## TO-220



Dimensions in Millimeters

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